MC74AC4040

12-Stage Binary Ripple Counter

The MC74AC4040 consists of 12 master-slave flip-flops. The output of each flip-flop feeds the next and the frequency at each output is half that of the preceding one. The state of the counter advances on the negative-going edge of the Clock input. Reset is asynchronous and active-high.

State changes of the Q outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and may have to be gated with the Clock of the MC74AC4040 for some designs.

- 140 MHz Typ. Clock
- Outputs Source/Sink 24 mA
- Operating Voltage Range: 2.0 to 6.0 V
- High Noise Immunity

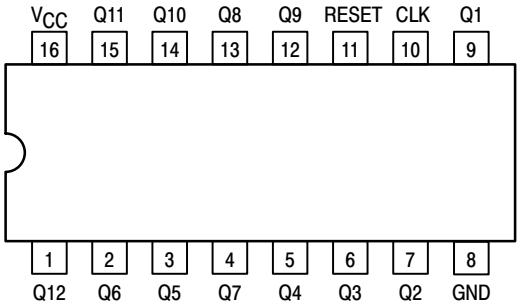

Figure 1. Pinout: 16–Lead Packages Conductors
(Top View)

FUNCTION TABLE

Clock	Reset	Output State
⎺_	L	No Change
_⎺	L	Advance to next state
X	H	All Outputs are low

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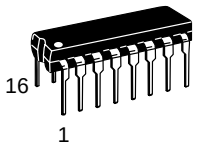
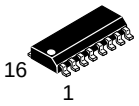
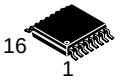


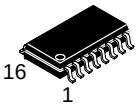
DIP–16
N SUFFIX
CASE 648



SO–16
D SUFFIX
CASE 751B



TSSOP–16
DT SUFFIX
CASE 948F



EIAJ–16
M SUFFIX
CASE 966

ORDERING INFORMATION

Device	Package	Shipping
MC74AC4040N	PDIP–16	25 Units/Rail
MC74AC4040D	SOIC–16	48 Units/Rail
MC74AC4040DR2	SOIC–16	2500 Tape & Reel
MC74AC4040DT	TSSOP–16	96 Units/Rail
MC74AC4040DTR2	TSSOP–16	2500 Tape & Reel
MC74AC4040M	EIAJ–16	50 Units/Rail

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 4 of this data sheet.

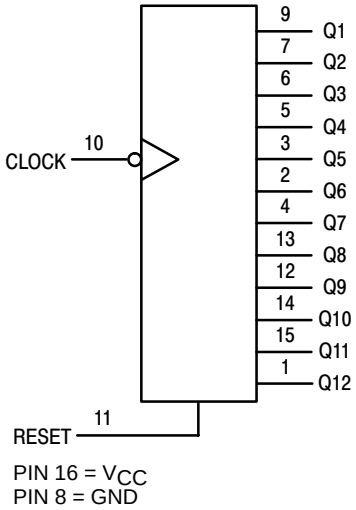


Figure 2. Logic Diagram

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	–0.5 to +7.0	V
V_{IN}	DC Input Voltage (Referenced to GND)	–0.5 to V_{CC} +0.5	V
V_{OUT}	DC Output Voltage (Referenced to GND)	–0.5 to V_{CC} +0.5	V
I_{IN}	DC Input Current, per Pin	±20	mA
I_{OUT}	DC Output Current, per Pin	±50	mA
I_{CC}	DC V_{CC} or GND Current per Output Pin	±50	mA
P_D	Power Dissipation in Still Air Plastic† SOIC Package†	 750 500	mW
T_{stg}	Storage Temperature	–65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 seconds (Plastic DIP or SOIC Package)	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur.
†Derating: Plastic DIP: – 10mW/°C from 65°C to 125°C SOIC Package: –7.0 mW/°C from 65°C to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V_{IN}/V_{OUT}	Input Voltage, Output Voltage (Ref. to GND)		0	V_{CC}	–
T_A	Operating Temperature, All Package Types		–40	+85	°C
t_r/t_f	Input Rise/Fall Time (Figure 1)	V_{CC} = 3.0 V V_{CC} = 4.5 V V_{CC} = 5.5 V	0 0 0	150 40 25	ns/V

DC CHARACTERISTICS (unless otherwise specified)

Symbol	Parameter	Value	Unit	
I_{CC}	Maximum Quiescent Supply Voltage	80	μA	$V_{in} = V_{CC}$ or GND V_{CC} = 5.5 V, T_A = Worst Case
I_{CC}	Maximum Quiescent Supply Current	8.0	μA	$V_{in} = V_{CC}$ or GND V_{CC} = 5.5 V, T_A = 25°C

DC CHARACTERISTICS

Symbol	Parameter	V_{CC} (V)	74AC	74AC	Unit	Conditions
			T_A = +25°C	T_A = –40°C to +85°C		
			Typ	Guaranteed Limits		
V_{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5	– – –	2.1 3.15 3.85	2.1 3.15 3.85	V	V_{OUT} = 0.1 V or V_{CC} – 0.1 V
V_{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	– – –	0.9 1.35 1.65	0.9 1.35 1.65	V	V_{OUT} = 0.1 V or V_{CC} – 0.1 V
V_{OH}	Minimum High Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V	I_{OUT} = –50 μA
		3.0 4.5 5.5	– – –	2.56 3.86 4.86	2.46 3.76 4.76	V	*V_{IN} = V_{IL} or V_{IH} –12 mA I_{OH} –24 mA –24 mA
V_{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	V	I_{OUT} = 50 μA
		3.0 4.5 5.5	– – –	0.36 0.36 0.36	0.44 0.44 0.44	V	*V_{IN} = V_{IL} or V_{IH} 12 mA I_{OL} 24 mA 24 mA
I_{IN}	Maximum Input Leakage Current	5.5	–	±0.1	±1.0	μA	V_I = V_{CC}, GND
I_{OLD}	Minimum Dynamic Output Current†	5.5	–	–	75	mA	V_{OLD} = 1.65 V Max
I_{OHD}		5.5	–	–	–75	mA	V_{OHD} = 3.85 V Min

*All outputs loaded; thresholds on input associated with output under test.
†Maximum test duration 2.0 ms, one output loaded at a time.

AC CHARACTERISTICS (For Figures and Waveforms – See Section 3 of the ON Semiconductor FACT Data Book, DL138/D)

Symbol	Parameter	V_{CC}* (V)	74AC T_A = +25°C C_L = 50 pF			74AC T_A = –40°C to +85°C C_L = 50 pF		Unit	Fig. No.
			Min	Typ	Max	Min	Max		
f_{max}	Maximum Clock Frequency	3.3 5.0	110 130	120 140	– –	100 120	– –	MHz	–
n_{CP} to Q1	Propagation Delay n_{CP} to Q1	3.3 5.0	2.0 2.0	– –	11 8.0	2.0 2.0	14 10	ns	–
Q_n to Q_n +1	Propagation Delay Q_n to Q_n +1	3.3 5.0	0 0	– –	5.5 3.5	0 0	6.5 4.5	ns	–
MR to Q t_{HL}	Propagation Delay MR to Q	3.3 5.0	3.0 3.0	– –	12 10	3.0 3.0	15 12	ns	–
t_{rec} n_{CP} to MR	Recovery Time	3.3 5.0	0 0	–2.5 –1.5	– –	0 0	– –	ns	–
t_W n_{CP}	Minimum Pulse Width Clock Pin	3.3 5.0	4.0 3.0	3.5 2.5	– –	4.5 3.5	– –	ns	–
t_W MR	Minimum Pulse Width Master Reset	3.3 3.0	4.0 3.0	3.5 2.5	– –	4.5 3.5	– –	ns	–

*Voltage Range 3.3 V is 3.3 V ±0.3 V.
*Voltage Range 5.0 V is 5.0 V ±0.5 V.

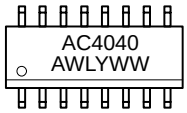
CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C_{IN}	Input Capacitance	4.5	pF	V_{CC} = 5.0 V
C_{PD}	Power Dissipation Capacitance	50	pF	V_{CC} = 5.0 V

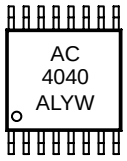
MARKING DIAGRAMS

DIP–16

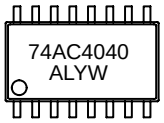
SO–16



TSSOP–16



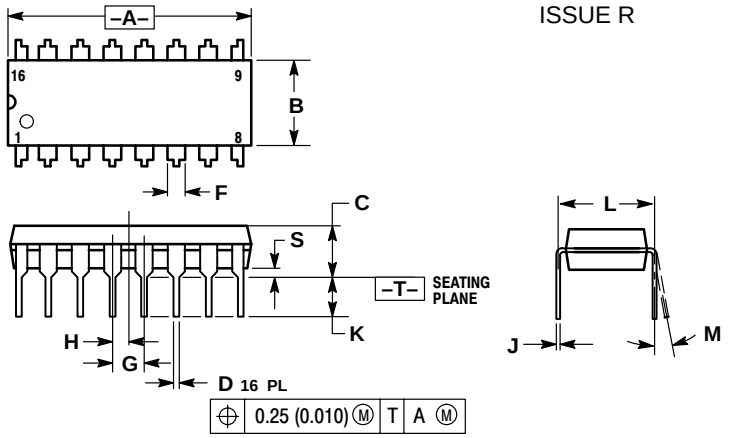
EIAJ–16



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week

PACKAGE DIMENSIONS

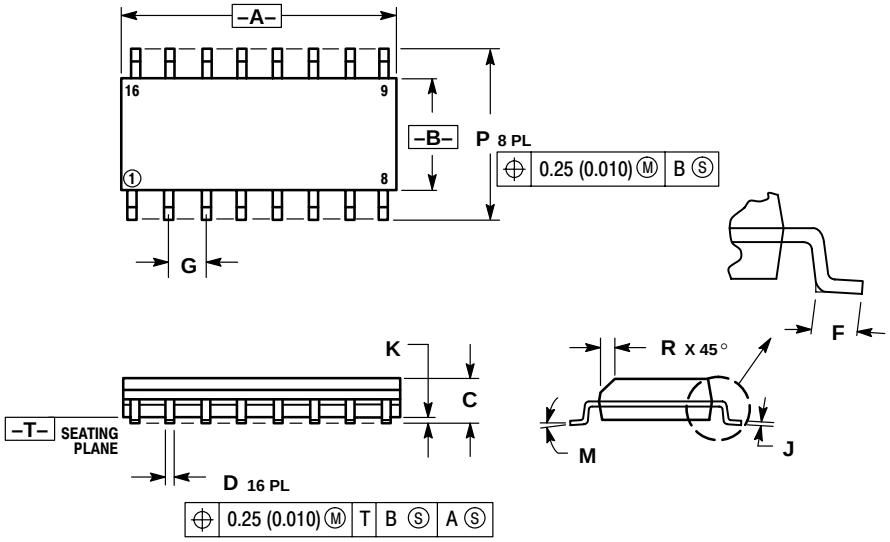
PDIP–16
N SUFFIX
16 PIN PLASTIC DIP PACKAGE
CASE 648–08
ISSUE R



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01

SO–16
D SUFFIX
16 PIN PLASTIC SOIC PACKAGE
CASE 751B–05
ISSUE J

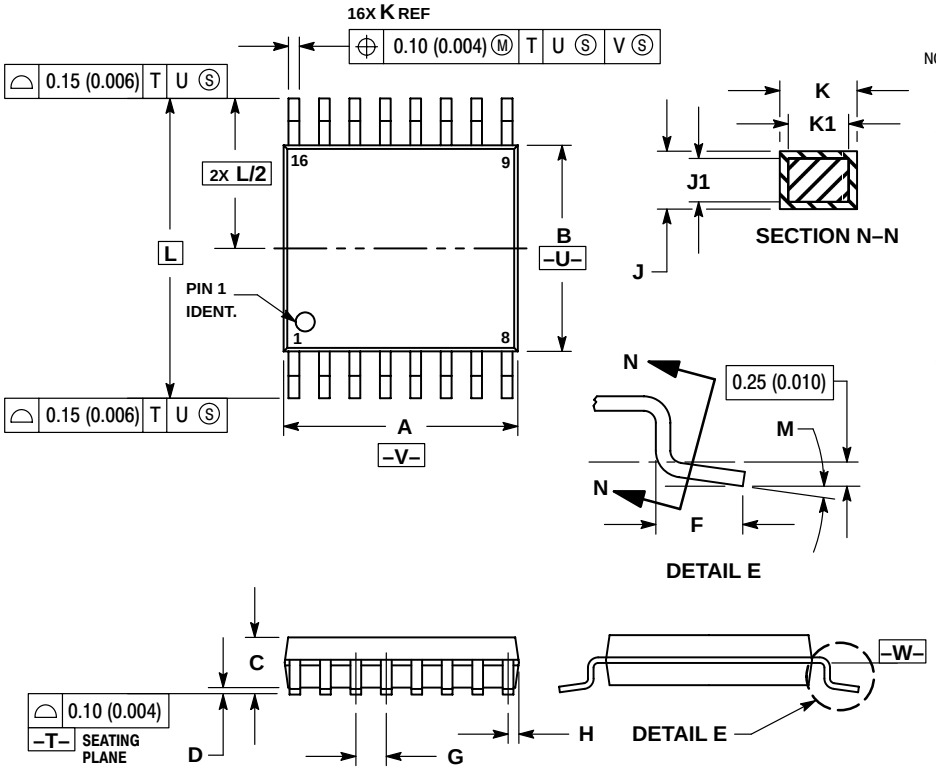


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

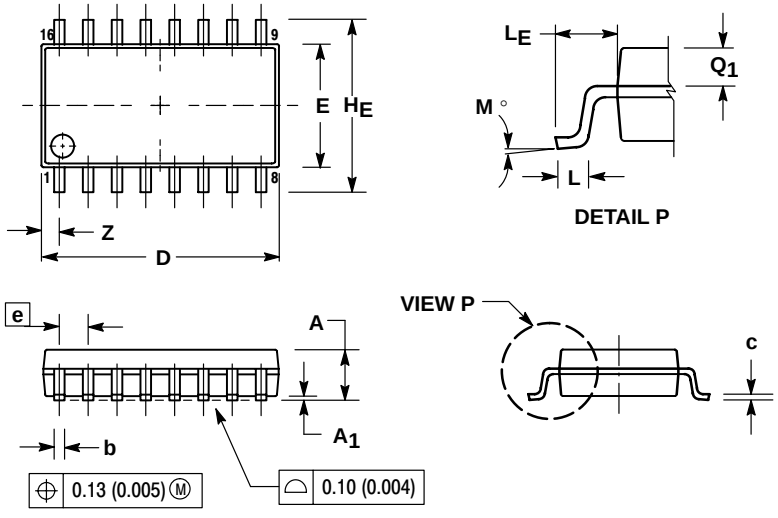
TSSOP–16
DT SUFFIX
16 PIN PLASTIC TSSOP PACKAGE
CASE948F–01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

EIAJ–16
M SUFFIX
16 PIN PLASTIC EIAJ PACKAGE
CASE966–01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	---	0.78	---	0.031

Notes

PUBLICATION ORDERING INFORMATION

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